

Akihiro Suzuki

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3179167/publications.pdf>

Version: 2024-02-01

10

papers

43

citations

1937685

4

h-index

1872680

6

g-index

10

all docs

10

docs citations

10

times ranked

14

citing authors

#	ARTICLE	IF	CITATIONS
1	Hydrogen passivation for reduction of SiO_{2} /Si interface state density using hydrocarbon-molecular-ion-implanted silicon wafers. <i>Japanese Journal of Applied Physics</i> , 2020, 59, 125502.	1.5	13
2	Reduction of Dark Current in CMOS Image Sensor Pixels Using Hydrocarbon-Molecular-Ion-Implanted Double Epitaxial Si Wafers. <i>Sensors</i> , 2020, 20, 6620.	3.8	9
3	Molecular and Atomic Hydrogen Diffusion Behavior by Reaction Kinetic Analysis in Projection Range of Hydrocarbon Molecular Ion for CMOS Image Sensors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900175.	1.8	5
4	Fundamental Characteristics of Cyanide-Related Multielement Molecular Ion-Implanted Epitaxial Si Wafers for High-Performance CMOS Image Sensors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900172.	1.8	5
5	Influence of oxygen on copper gettering in hydrocarbon molecular ion implanted region using atom probe tomography. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2020, 478, 99-103.	1.4	4
6	Proximity gettering design of silicon wafers using silicon hydride and hydrocarbon mixture molecular ion implantation technique. <i>Materials Science in Semiconductor Processing</i> , 2021, 135, 106063.	4.0	3
7	Hydrogen diffusion behavior in CH ₂ P-molecular-ion-implanted silicon wafers for CMOS image sensors. <i>Materials Science in Semiconductor Processing</i> , 2022, 137, 106211.	4.0	1
8	Effect of ramping up rate on end of range defect in multielement molecular-ion (CH_3O)-implanted silicon wafers. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 121002.	1.5	1
9	Photoemission Spectroscopy Study on Hydrogen Termination Effect on SiO_2/Si Structure Fabricated Using H+-Implanted Si Substrate. <i>Journal of the Electrochemical Society</i> , 2020, 167, 127505.	2.9	1
10	In Situ Transmission Electron Microscopy Study of Shrinkage Kinetics of CH ₄ -N-Molecular-Ion-Implantation-Induced Extended Defects. <i>Journal of the Electrochemical Society</i> , 2022, 169, 047521.	2.9	1